

# Anthony J Kenyon

## List of Publications by Year in descending order

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152  
papers

5,810  
citations

101543  
36  
h-index

79698  
73  
g-index

156  
all docs

156  
docs citations

156  
times ranked

5739  
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent developments in rare-earth doped materials for optoelectronics. Progress in Quantum Electronics, 2002, 26, 225-284.	7.0	777
2	Recommended Methods to Study Resistive Switching Devices. Advanced Electronic Materials, 2019, 5, 1800143.	5.1	452
3	Erbium in silicon. Semiconductor Science and Technology, 2005, 20, R65-R84.	2.0	238
4	Resistive switching in silicon suboxide films. Journal of Applied Physics, 2012, 111, .	2.5	217
5	Optical properties of PECVD erbium-doped silicon-rich silica: evidence for energy transfer between silicon microclusters and erbium ions. Journal of Physics Condensed Matter, 1994, 6, L319-L324.	1.8	208
6	The origin of photoluminescence from thin films of silicon-rich silica. Journal of Applied Physics, 1996, 79, 9291-9300.	2.5	207
7	Modeling the contribution of quantum confinement to luminescence from silicon nanoclusters. Journal of Applied Physics, 1998, 83, 3789-3794.	2.5	184
8	Luminescence from erbium-doped silicon nanocrystals in silica: Excitation mechanisms. Journal of Applied Physics, 2002, 91, 367.	2.5	162
9	Silicon Oxide ( $\text{SiO}_x$ ): A Promising Material for Resistance Switching?. Advanced Materials, 2018, 30, e1801187.	21.0	156
10	Brain-inspired computing needs a master plan. Nature, 2022, 604, 255-260.	27.8	147
11	Quantum Conductance in Silicon Oxide Resistive Memory Devices. Scientific Reports, 2013, 3, 2708.	3.3	144
12	Memristors—From In-Memory Computing, Deep Learning Acceleration, and Spiking Neural Networks to the Future of Neuromorphic and Bio-Inspired Computing. Advanced Intelligent Systems, 2020, 2, 2000085.	6.1	143
13	Evidence of energy coupling between Si nanocrystals and $\text{Er}^{3+}$ in ion-implanted silica thin films. Applied Physics Letters, 1999, 75, 2011-2013.	3.3	135
14	Standards for the Characterization of Endurance in Resistive Switching Devices. ACS Nano, 2021, 15, 17214-17231.	14.6	128
15	Emulating the Electrical Activity of the Neuron Using a Silicon Oxide RRAM Cell. Frontiers in Neuroscience, 2016, 10, 57.	2.8	106
16	Structural changes and conductance thresholds in metal-free intrinsic $\text{SiO}_x$ resistive random access memory. Journal of Applied Physics, 2015, 117, .	2.5	102
17	Electrically tailored resistance switching in silicon oxide. Nanotechnology, 2012, 23, 455201.	2.6	96
18	Losses in luminescent solar concentrators unveiled. Solar Energy Materials and Solar Cells, 2016, 144, 40-47.	6.2	82

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19	Complementary Metalâ€Oxide Semiconductor and Memristive Hardware for Neuromorphic Computing. Advanced Intelligent Systems, 2020, 2, 1900189.	6.1	78
20	Towards population inversion of electrically pumped Er ions sensitized by Si nanoclusters. Optics Express, 2010, 18, 2230.	3.4	77
21	FTIR and XPS investigation of Er-doped SiO2â€TiO2 films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 209-213.	3.5	70
22	The vapour phase detection of explosive markers and derivatives using two fluorescent metalâ€organic frameworks. Journal of Materials Chemistry A, 2015, 3, 6351-6359.	10.3	69
23	Intrinsic resistance switching in amorphous silicon oxide for high performance SiOx ReRAM devices. Microelectronic Engineering, 2017, 178, 98-103.	2.4	64
24	Conductance tomography of conductive filaments in intrinsic silicon-rich silica RRAM. Nanoscale, 2015, 7, 18030-18035.	5.6	62
25	On the ability of FÃrster resonance energy transfer to enhance luminescent solar concentrator efficiency. Nano Energy, 2017, 32, 263-270.	16.0	60
26	Self-assembly of metallic nanoparticles into one dimensional arrays. Journal of Materials Chemistry A, 2013, 1, 6985.	10.3	54
27	Sensing and Discrimination of Explosives at Variable Concentrations with a Large-Pore MOF as Part of a Luminescent Array. ACS Applied Materials & Interfaces, 2019, 11, 11618-11626.	8.0	54
28	Nanoscale Transformations in Metastable, Amorphous, Siliconâ€Rich Silica. Advanced Materials, 2016, 28, 7486-7493.	21.0	52
29	Simulation of Inference Accuracy Using Realistic RRAM Devices. Frontiers in Neuroscience, 2019, 13, 593.	2.8	52
30	Amorphous and nanocrystalline luminescent Si and Ge obtained via a solid-state chemical metathesis synthesis route. Journal of Solid State Chemistry, 2005, 178, 937-949.	2.9	51
31	Committee machinesâ€a universal method to deal with non-idealities in memristor-based neural networks. Nature Communications, 2020, 11, 4273.	12.8	51
32	Light-activated resistance switching in SiOx RRAM devices. Applied Physics Letters, 2017, 111, .	3.3	47
33	Electrospray synthesis and properties of hierarchically structured PLGA TIPS microspheres for use as controlled release technologies. Journal of Colloid and Interface Science, 2016, 467, 220-229.	9.4	46
34	Current transport and electroluminescence mechanisms in thin SiO2 films containing Si nanocluster-sensitized erbium ions. Journal of Applied Physics, 2009, 106, .	2.5	45
35	Probing the phonon confinement in ultrasmall silicon nanocrystals reveals a size-dependent surface energy. Journal of Applied Physics, 2011, 109, 083534.	2.5	45
36	Intrinsic Resistance Switching in Amorphous Silicon Suboxides: The Role of Columnar Microstructure. Scientific Reports, 2017, 7, 9274.	3.3	41

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37	The interaction of gold and silver nanoparticles with a range of anionic and cationic dyes. Physical Chemistry Chemical Physics, 2014, 16, 6050-6059.	2.8	37
38	Modeling of Quantized Conductance Effects in Electrochemical Metallization Cells. IEEE Nanotechnology Magazine, 2015, 14, 505-512.	2.0	33
39	Er <sup>3+</sup> excited state absorption and the low fraction of nanocluster-excitable Er <sup>3+</sup> in SiO <sub>x</sub> . Applied Physics Letters, 2006, 89, 031116.	3.3	32
40	Quantum confinement in rare-earth doped semiconductor systems. Current Opinion in Solid State and Materials Science, 2003, 7, 143-149.	11.5	31
41	Homeotropic alignment and Förster resonance energy transfer: The way to a brighter luminescent solar concentrator. Journal of Applied Physics, 2014, 116, 173103.	2.5	31
42	Liquid surface dynamics: a quantum-resolved scattering study. Chemical Physics Letters, 1992, 190, 55-58.	2.6	28
43	Efficiency and loss mechanisms of plasmonic Luminescent Solar Concentrators. Optics Express, 2013, 21, A735.	3.4	28
44	Probing electrochemistry at the nanoscale: in situ TEM and STM characterizations of conducting filaments in memristive devices. Journal of Electroceramics, 2017, 39, 73-93.	2.0	28
45	Flexible and fluorophore-doped luminescent solar concentrators based on polydimethylsiloxane. Optics Letters, 2016, 41, 713.	3.3	27
46	Investigation of dynamical processes at liquid surfaces by molecular scattering. Journal of the Chemical Society, Faraday Transactions, 1993, 89, 3877.	1.7	26
47	Generalized rate-equation analysis of excitation exchange between silicon nanoclusters and erbium ions. Physical Review B, 2008, 77, .	3.2	26
48	Luminescence efficiency measurements of silicon nanoclusters. Applied Physics Letters, 1998, 73, 523-525.	3.3	24
49	Spike-Timing Dependent Plasticity in Unipolar Silicon Oxide RRAM Devices. Frontiers in Neuroscience, 2018, 12, 57.	2.8	24
50	Investigation of resistance switching in SiO <sub>x</sub> RRAM cells using a 3D multi-scale kinetic Monte Carlo simulator. Journal of Physics Condensed Matter, 2018, 30, 084005.	1.8	23
51	The origin of the 0.78 eV luminescence band in dislocated silicon. Journal of Physics Condensed Matter, 2003, 15, S2843-S2850.	1.8	21
52	Investigation of quartz grain surface textures by atomic force microscopy for forensic analysis. Forensic Science International, 2012, 223, 245-255.	2.2	21
53	Microscopic and spectroscopic analysis of the nature of conductivity changes during resistive switching in silicon-rich silicon oxide. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 211-217.	0.8	21
54	Multi-channel conduction in redox-based resistive switch modelled using quantum point contact theory. Applied Physics Letters, 2013, 103, .	3.3	19

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55	Doping Group IIB Metal Ions into Quantum Dot Shells via the One-Pot Decomposition of Metal-Dithiocarbamates. <i>Advanced Optical Materials</i> , 2015, 3, 704-712.	7.3	19
56	On the Limits of Scalpel AFM for the 3D Electrical Characterization of Nanomaterials. <i>Advanced Functional Materials</i> , 2018, 28, 1802266.	14.9	19
57	Remote-coupled sensing of plasma harmonics and process end-point detection. <i>Vacuum</i> , 2000, 57, 351-364.	3.5	18
58	Dynamics of the gas/liquid interface from laser molecular beam scattering. <i>Faraday Discussions</i> , 1993, 96, 245.	3.2	17
59	Nonideality-Aware Training for Accurate and Robust Low-Power Memristive Neural Networks. <i>Advanced Science</i> , 2022, 9, e2105784.	11.2	17
60	Fluorescence depolarization as a probe of molecular dynamics within liquid jets. <i>Molecular Physics</i> , 1991, 72, 965-970.	1.7	16
61	Indirect excitation of 1.5 $\mu$ m emission from Er <sup>3+</sup> in silicon-rich silica. <i>Applied Physics Letters</i> , 2000, 76, 688-690.	3.3	16
62	An analysis of erbium excited state absorption in silicon-rich silica. <i>Journal of Luminescence</i> , 2006, 121, 193-198.	3.1	16
63	Self-Assembled Ultra-High Aspect Ratio Silver Nanochains. <i>Advanced Materials</i> , 2012, 24, 5227-5235.	21.0	16
64	Resistive Switching in Oxides. <i>Springer Series in Surface Sciences</i> , 2015, , 401-428.	0.3	16
65	<i>In situ</i> transmission electron microscopy of resistive switching in thin silicon oxide layers. <i>Resolution and Discovery</i> , 2016, 1, 27-33.	0.4	16
66	The interplay between structure and function in redox-based resistance switching. <i>Faraday Discussions</i> , 2019, 213, 151-163.	3.2	16
67	An oxygen vacancy mediated Ag reduction and nucleation mechanism in SiO <sub>2</sub> RRAM devices. <i>Microelectronics Reliability</i> , 2019, 98, 144-152.	1.7	16
68	Structural factors impacting carrier transport and electroluminescence from Si nanocluster-sensitized Er ions. <i>Optics Express</i> , 2012, 20, 22490.	3.4	15
69	A study of molecular dynamics within liquid flows using fluorescence depolarization. <i>Molecular Physics</i> , 1991, 74, 871-884.	1.7	14
70	Probing energy transfer in an ensemble of silicon nanocrystals. <i>Journal of Applied Physics</i> , 2011, 110, 033522.	2.5	14
71	Memristor-Based Edge Detection for Spike Encoded Pixels. <i>Frontiers in Neuroscience</i> , 2020, 13, 1386.	2.8	14
72	Rf probe technology for the next generation of technological plasmas. <i>Journal Physics D: Applied Physics</i> , 2001, 34, 2726-2733.	2.8	13

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73	Modification of the Er <sup>3+</sup> radiative lifetime from proximity to silicon nanoclusters in silicon-rich silicon oxide. Optics Express, 2009, 17, 906.	3.4	13
74	Silica: Nanoscale Transformations in Metastable, Amorphous, Silicon-Rich Silica (Adv. Mater. 34/2016). Advanced Materials, 2016, 28, 7549-7549.	21.0	13
75	Nanosecond Analog Programming of Substoichiometric Silicon Oxide Resistive RAM. IEEE Nanotechnology Magazine, 2016, 15, 428-434.	2.0	13
76	Memristive, Spintronic, and 2D-Materials-Based Devices to Improve and Complement Computing Hardware. Advanced Intelligent Systems, 2022, 4, .	6.1	13
77	Continuous hydrothermal synthesis of surface-functionalised nanophosphors for biological imaging. RSC Advances, 2012, 2, 10037.	3.6	12
78	X-ray spectromicroscopy investigation of soft and hard breakdown in RRAM devices. Nanotechnology, 2016, 27, 345705.	2.6	11
79	High-Performance Resistance Switching Memory Devices Using Spin-On Silicon Oxide. IEEE Nanotechnology Magazine, 2018, 17, 884-888.	2.0	11
80	DC electroluminescence from PECVD grown thin films of silicon-rich silica. Electronics Letters, 1996, 32, 1703.	1.0	10
81	Broadband sensitization of 1.53 $\mu$ m Er <sup>3+</sup> luminescence in erbium-implanted alumina. Applied Physics Letters, 2004, 85, 5200-5202.	3.3	10
82	Excited state absorption in the Si nanocluster-Er material system. IEEE Photonics Technology Letters, 2006, 18, 289-291.	2.5	10
83	Donor ionization in size controlled silicon nanocrystals: The transition from defect passivation to free electron generation. Journal of Applied Physics, 2013, 113, 024304.	2.5	10
84	Investigation of energy exchange between silicon nanocrystals and Er <sup>3+</sup> in silica. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 16-18.	3.5	9
85	‘It’s Not for Lazy Students like Me’. International Journal of Electrical Engineering and Education, 2005, 42, 41-51.	0.8	9
86	Broad-band and flashlamp pumping of 1.53 $\mu$ m emission from erbium-doped silicon nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 19-22.	3.5	8
87	Increasing the efficiency of erbium-based sources using silicon quantum dots. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2003, 361, 345-362.	3.4	8
88	Introducing scenario based learning: Experiences from an undergraduate electronic and electrical engineering course. , 2010, , .		8
89	Visible photoluminescence from nanocrystalline Ge grown at room temperature by photo-oxidation of SiGe using a 126 nm lamp. Applied Surface Science, 2003, 208-209, 364-368.	6.1	7
90	Modification of erbium photoluminescence decay rate due to ITO layers on thin films of SiO <sub>2</sub> :Er doped with Si-nanoclusters. Journal of Luminescence, 2013, 136, 407-410.	3.1	7

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91	Multiple Diode-Like Conduction in Resistive Switching SiO <sub>2</sub> -Based MIM Devices. IEEE Nanotechnology Magazine, 2015, 14, 15-17.	2.0	7
92	Design and Fabrication of Suspended Indium Phosphide Waveguides for MEMS-Actuated Optical Buffering. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 240-246.	2.9	7
93	Conductive AFM Topography of Intrinsic Conductivity Variations in Silica Based Dielectrics for Memory Applications. ECS Transactions, 2016, 75, 3-9.	0.5	7
94	Simulation of Cycle-to-Cycle Instabilities in SiO <sub>x</sub> -Based ReRAM Devices Using a Self-Correlated Process with Long-Term Variation. IEEE Electron Device Letters, 2018, , 1-1.	3.9	7
95	A noninvasive rf probe for the study of ionization and dissociation processes in technological plasmas. Journal of Applied Physics, 1999, 86, 4100-4106.	2.5	6
96	A frequency domain measurement diagnostic technique for plasma-tools. Measurement Science and Technology, 2004, 15, 231-236.	2.6	6
97	Rate equation modelling of erbium luminescence dynamics in erbium-doped silicon-rich-silicon-oxide. Journal of Luminescence, 2012, 132, 3103-3112.	3.1	6
98	Advanced physical modeling of SiO <sub>2</sub> ; resistive random access memories. , 2016, , .		6
99	A nanoscale analysis method to reveal oxygen exchange between environment, oxide, and electrodes in ReRAM devices. APL Materials, 2021, 9, .	5.1	6
100	Retention of data in heat-damaged SIM cards and potential recovery methods. Forensic Science International, 2008, 177, 42-46.	2.2	5
101	Electrically pumped silicon waveguide light sources. Optics Express, 2011, 19, 24569.	3.4	5
102	Size limit on the phosphorous doped silicon nanocrystals for dopant activation. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 456-458.	1.4	5
103	Improving the Consistency of Nanoscale Etching for Atomic Force Microscopy Tomography Applications. Frontiers in Materials, 2019, 6, .	2.4	5
104	Electrochemical metallization ReRAMs (ECM) - Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 115-150.	3.2	5
105	Substitutional Tin Acceptor States in Black Phosphorus. Journal of Physical Chemistry C, 2021, 125, 22883-22889.	3.1	5
106	Process harmonic pulling in RIE plasma-tool. Electronics Letters, 2006, 42, 120.	1.0	4
107	Time-resolved measurements of dislocation-related photoluminescence bands in silicon. Semiconductor Science and Technology, 2008, 23, 025010.	2.0	4
108	Time-correlated single-photon counting study of multiple photoluminescence lifetime components of silicon nanoclusters. Journal of Luminescence, 2013, 136, 57-62.	3.1	4

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109	Controlling and modelling the wetting properties of III-V semiconductor surfaces using re-entrant nanostructures. Scientific Reports, 2018, 8, 3544.	3.3	4
110	Thermal effects in scanning acoustic microscopy for fine resolution applications. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 1994, 41, 565-568.	3.0	3
111	Rare-Earth Doped Silicon-Rich Silica: Evidence for Energy Transfer between Silicon Microclusters and Rare-Earth Ions. Materials Research Society Symposia Proceedings, 1994, 358, 117.	0.1	3
112	The infra-red photoresponse of erbium-doped silicon nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 230-235.	3.5	3
113	Silicon nanocluster-sensitized emission from erbium: The role of stress in the formation of silicon nanoclusters. Journal of Applied Physics, 2008, 104, .	2.5	3
114	A Planar CMOS Field-Emission Vacuum Magnetic Sensor. IEEE Transactions on Electron Devices, 2009, 56, 692-695.	3.0	3
115	Neuromorphic Dynamics at the Nanoscale in Silicon Suboxide RRAM. Frontiers in Nanotechnology, 2021, 3, .	4.8	3
116	Enhancement of Er emission by coupling to silicon nanoclusters: a route to flashlamp-pumped Er amplifiers?. , 2001, , .		2
117	Flashlamp pumping of erbium-doped silicon nanoclusters. Applied Organometallic Chemistry, 2001, 15, 352-358.	3.5	2
118	Harmonic monitoring of the switched silicon etched process. Journal Physics D: Applied Physics, 2003, 36, 2146-2151.	2.8	2
119	Sensitisation of erbium luminescence in erbium-implanted alumina. Optical Materials, 2006, 28, 655-659.	3.6	2
120	Silicon nanoclusters containing nitrogen and sensitization of erbium luminescence in SiO <sub>x</sub> :Er. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 175-178.	3.5	2
121	Synaptic and neuromorphic functions: general discussion. Faraday Discussions, 2019, 213, 553-578.	3.2	2
122	Valence change ReRAMs (VCM) - Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 259-286.	3.2	2
123	The nature of column boundaries in micro-structured silicon oxide nanolayers. APL Materials, 2021, 9, 121107.	5.1	2
124	Mitigating Non-idealities of Memristive-based Artificial Neural Networks - an Algorithmic Approach. , 2022, , .		2
125	Non-Destructive Assessment Of Semiconductor Carrier Lifetime Using Photothermal Radiometry. Materials Research Society Symposia Proceedings, 1996, 428, 455.	0.1	1
126	Time-resolved measurements of dislocation-related photoluminescence bands in silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1811-1816.	0.8	1



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127	MEMS actuation for a continuously tunable optical buffer. , 2014, , .		1
128	Design and fabrication of InP free-standing optical waveguides for MEMS. , 2014, , .		1
129	Resistance Switching in Individual Hydrogen Silsesquioxane (HSQ) Nanopillars. ECS Transactions, 2016, 75, 101-105.	0.5	1
130	Theoretical Study of Ag Interactions in Amorphous Silica RRAM Devices. , 2018, , .		1
131	Engineering Silicon Oxide by Argon Ion Implantation for High Performance Resistance Switching. Frontiers in Materials, 2022, 9, .	2.4	1
132	Thermo-acoustic effects on images for high resolution scanning acoustic microscopy. Electronics Letters, 1994, 30, 127-128.	1.0	0
133	Silicon Nanoclusters In Silica: A Luminescence Study Of Visible Light Emission From A Siliconbased Material. Materials Research Society Symposia Proceedings, 1996, 424, 483.	0.1	0
134	Investigation of Coupling Mechanism between Erbium (Er <sup>3+</sup> ) and Ytterbium (Yb <sup>3+</sup> ) in Alumina (Al <sub>2</sub> O <sub>3</sub> ) Host. Materials Research Society Symposia Proceedings, 1999, 560, 203.	0.1	0
135	THE EFFECT OF LEVEL MIXING IN Er-DOPED Si. Materials Research Society Symposia Proceedings, 1999, 560, 251.	0.1	0
136	Energy Transfer in Erbium-Doped Silicon Nanoclusters: A Comparison of Silicon-Rich Silica and Silicon Nanopowders. Materials Research Society Symposia Proceedings, 1999, 560, 221.	0.1	0
137	Photoluminescence characterization of Er <sup>3+</sup> -implanted silica thin films containing Si nanocrystals. , 2000, , .		0
138	A Silicon-Based Infra-Red Photodetector Exploiting Erbium-Doped Silicon Nanocrystals. Materials Research Society Symposia Proceedings, 2003, 770, 6111.	0.1	0
139	The Origin Of The 0.78 eV Luminescence Band In Strained Layer SiGe/Si. Materials Research Society Symposia Proceedings, 2003, 770, 511.	0.1	0
140	Rare earth doped photonic materials. Optical Materials, 2006, 28, v.	3.6	0
141	Study of the electroluminescence at 1.5 $\mu\text{m}$ of SiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> /Si <sub>3</sub> N <sub>4</sub> /Si <sub>3</sub> N <sub>4</sub> /Si <sub>3</sub> N <sub>4</sub> :Er layers made by reactive magnetron sputtering. , 2009, , .		0
142	(Invited) Novel Processing for Si-Nanocrystal Based Photonic Materials. ECS Transactions, 2010, 28, 3-13.	0.5	0
143	Intrinsic Resistive Switching in Bulk SiO <sub>x</sub> Films. Materials Research Society Symposia Proceedings, 2012, 1430, 1.	0.1	0
144	(Invited) On the Origin of the Step-Like Quantum Yield of Si-Nanocrystals: MEG or Efficient Exciton Generation Via Critical Points in C-si. ECS Meeting Abstracts, 2013, , .	0.0	0

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145	(Invited) Resistive Switching in Silicon Oxide Containing Silicon Nano-inclusions. ECS Meeting Abstracts, 2013, , .	0.0	0
146	Development of Indium Phosphide MEMS for tunable optical buffering. , 2015, , .		0
147	Resistance switching in SiO <sub>x</sub> . , 2015, , .		0
148	Design and fabrication of indium phosphide air-bridge waveguides with MEMS functionality. Proceedings of SPIE, 2015, , .	0.8	0
149	Electrospun fabrication of one-dimensional composite nanofibres using colloidal gold/polymer aqueous blends. , 2015, , .		0
150	Structural investigation of resistance switching in silicon-rich silica films. , 2015, , .		0
151	Tunable optical buffer based on III-V MEMS design. , 2015, , .		0
152	Probing Electrochemistry at the Nanoscale: In Situ TEM and STM Characterizations of Conducting Filaments in Memristive Devices. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 87-120.	0.5	0